2-Bit 20 Mb/s Dual-Supply Level Translator

The NLSX4373 is a 2-bit configurable dual-supply bidirectional auto sensing translator that does not require a directional control pin. The V_{CC} I/O and V_L I/O ports are designed to track two different power supply rails, V_{CC} and V_L respectively. The V_{CC} supply rail is configurable from 1.5 V to 5.5 V while V_L supply rail is configurable to 1.5 V to 5.5 V. This allows voltage logic signals on the V_L side to be translated into lower, higher or equal value voltage logic signals on the V_{CC} side, and vice-versa.

The NLSX4373 translator has open–drain outputs with integrated 10 k Ω pullup resistors on the I/O lines. The integrated pullup resistors are used to pullup the I/O lines to either V_L or V_{CC}. The NLSX4373 is an excellent match for open–drain applications such as the I²C communication bus.

Features

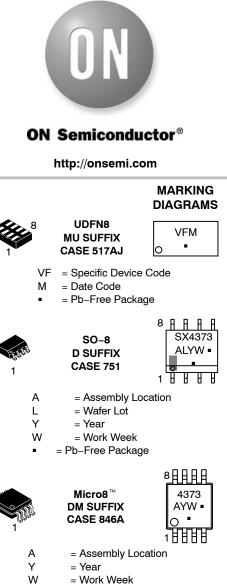
- V_L can be Less than, Greater than or Equal to V_{CC}
- Wide V_{CC} Operating Range: 1.5 V to 5.5 V Wide V_L Operating Range: 1.5 V to 5.5 V
- High-Speed with 20 Mb/s Guaranteed Date Rate
- Low Bit-to-Bit Skew
- Enable Input and I/O Lines have Overvoltage Tolerant (OVT) to 5.5 V
- Nonpreferential Powerup Sequencing
- Integrated 10 kΩ Pullup Resistors
- Small packaging: UDFN8, SO-8, Micro8
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable*
- This is a Pb–Free Device

Typical Applications

- I²C, SMBus, PMBus
- Low Voltage ASIC Level Translation
- Mobile Phones, PDAs, Cameras

Important Information

- ESD Protection for All Pins
 - Human Body Model (HBM) > 7000 V



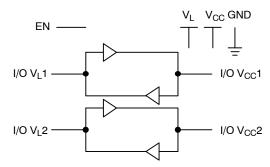
= Pb-Free Package

ORDERING INFORMATION

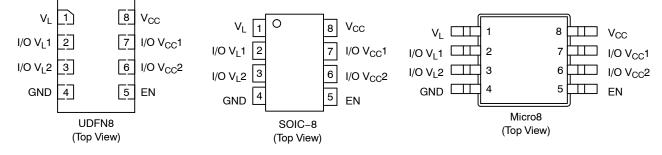
Device	Package	Shipping [†]				
NLSX4373MUTAG	UDFN8 (Pb-Free)	3000/Tape & Reel				
NLVSX4373MUTAG*	UDFN8 (Pb-Free)	3000/Tape & Reel				
NLSX4373DR2G	SO-8 (Pb-Free)	2500/Tape & Reel				
NLVSX4373DR2G*	SO-8 (Pb-Free)	2500/Tape & Reel				
NLSX4373DMR2G	Micro8 (Pb-Free)	4000/Tape & Reel				

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

LOGIC DIAGRAM



PIN ASSIGNMENTS



PIN ASSIGNMENT

Pins	Description	
V _{CC}	V _{CC} Input Voltage	
VL	V _L Input Voltage	
GND	Ground	
EN	Output Enable	
I/O V _{CC} n	V_{CC} I/O Port, Referenced to V_{CC}	
I/O V _L n	V_L I/O Port, Referenced to V_L	

FUNCTION TABLE

EN	Operating Mode
L	Hi–Z
Н	I/O Buses Connected

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	High-side DC Supply Voltage	-0.3 to +7.0		V
VL	High-side DC Supply Voltage	-0.3 to +7.0		V
I/O V _{CC}	V _{CC} -Referenced DC Input/Output Voltage	-0.3 to (V _{CC} + 0.3)		V
I/O V _L	V _L -Referenced DC Input/Output Voltage	–0.3 to (V _L + 0.3)		V
V_{EN}	Enable Control Pin DC Input Voltage	-0.3 to +7.0		V
I _{I/O_SC}	Short–Circuit Duration (I/O V_L and I/O V_{CC} to GND)	40	Continuous	mA
T _{STG}	Storage Temperature	-65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Мах	Unit
V _{CC}	High-side Positive DC Supply Voltage	1.5	5.5	V
VL	High-side Positive DC Supply Voltage	1.5	5.5	V
V _{EN}	Enable Control Pin Voltage	GND	5.5	V
V _{IO}	Enable Control Pin Voltage	GND	5.5	V
T _A	Operating Temperature Range	-40	+85	°C

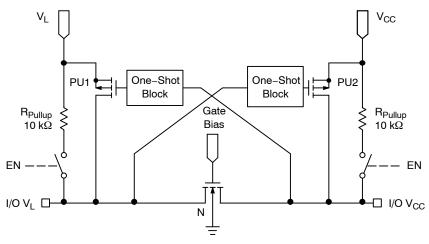


Figure 1. Block Diagram (1 I/O Line)

			-	40°C to +85°	0	
Symbol	Parameter	Test Conditions	Min	Typ (Notes 1, 2)	Max	Unit
VIHC	I/O V _{CC} Input HIGH Voltage		V _{CC} - 0.4	-	-	V
V _{ILC}	I/O V _{CC} Input LOW Voltage		-	-	0.15	V
V _{IHL}	I/O V _L Input HIGH Voltage		V _L – 0.2	-	-	V
V_{ILL}	I/O V _L Input LOW Voltage		-	-	0.15	V
V_{IH}	Control Pin Input HIGH Voltage		V _L – 0.2	-	-	V
V_{IL}	Control Pin Input LOW Voltage		-	-	0.15	V
V _{OHC}	I/O V _{CC} Output HIGH Voltage	I/O V _{CC} Source Current = 20 μ A	2/3 * V _{CC}	-	-	V
V _{OLC}	I/O V _{CC} Output LOW Voltage	I/O V _{CC} Sink Current = 20 μ A	-	-	1/3 * V _{CC}	V
V _{OHL}	I/O V _L Output HIGH Voltage	I/O V _L Source Current = 20 μ A	2/3 * V _L	-	-	V
V _{OLL}	I/O V _L Output LOW Voltage	I/O V _L Sink Current = 20 μ A	-	-	1/3 * V _L	V
I _{QVCC}	V _{CC} Supply Current	I/O V _{CC} and I/O V _L Unconnected, V_{EN} = V _L	-	0.5	2.0	μΑ
I _{QVL}	V _L Supply Current	I/O V _{CC} and I/O V _L Unconnected, $V_{\rm EN}$ = V _L	-	0.3	1.5	μΑ
I _{TS-VCC}	V _{CC} Tristate Output Mode Supply Current	I/O V _{CC} and I/O V _L Unconnected, $V_{EN} = GND$	-	0.1	1.0	μΑ
I_{TS-VL}	V _L Tristate Output Mode Supply Current	I/O V _{CC} and I/O V _L Unconnected, $V_{EN} = \text{GND}$	-	0.1	1.0	μΑ
I _{OZ}	I/O Tristate Output Mode Leakage Current	$T_A = +25^{\circ}C$	-	0.1	1.0	μA
R _{PU}	Pullup Resistor I/O V _L and V _{CC}	T _A = +25°C	-	10	-	kΩ

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 1.5 V to 5.5 V and V_L = 1.5 V to 5.5 V, unless otherwise specified)

1. Typical values are for V_{CC} = +2.8 V, V_L = +1.8 V and T_A = +25°C. 2. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS - RAIL-TO-RAIL DRIVING CONFIGURATIONS

(I/O test circuit of Figures 2 and 3, C_{LOAD} = 15 pF, driver output impedance \leq 50 Ω , R_{LOAD} = 1 M Ω)

			- 40°C to +85°C (Notes 3 and 4)			
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _L = 1.5 V, V	/ _{CC} = 5.5 V					
t _{RVCC}	I/O V _{CC} Risetime				15	ns
t _{FVCC}	I/O V _{CC} Falltime				20	ns
t _{RVL}	I/O V _L Risetime				30	ns
t _{FVL}	I/O V _L Falltime				10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				20	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				20	ns
t _{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s
V _L = 1.8 V, V	/ _{CC} = 2.8 V					
t _{RVCC}	I/O V _{CC} Risetime				15	ns
t _{FVCC}	I/O V _{CC} Falltime				15	ns
t _{RVL}	I/O V _L Risetime				25	ns
t _{FVL}	I/O V _L Falltime				10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				15	ns
t _{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s
V _L = 2.5 V, V	/ _{CC} = 3.6 V					
t _{RVCC}	I/O V _{CC} Risetime				15	ns
t _{FVCC}	I/O V _{CC} Falltime				10	ns
t _{RVL}	I/O V _L Risetime				15	ns
t _{FVL}	I/O V _L Falltime				10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				15	ns
t PPSKEW	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s
V _L = 2.8 V, V	/ _{CC} = 1.8 V	I			1	
t _{RVCC}	I/O V _{CC} Risetime				25	ns
t _{FVCC}	I/O V _{CC} Falltime				10	ns
t _{RVL}	I/O V _L Risetime				20	ns
t _{FVL}	I/O V _L Falltime				15	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				15	ns
t PPSKEW	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

3. Typical values are for V_{CC} = +3.3 V, V_L = +1.8 V and T_A = +25°C. 4. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS - RAIL-TO-RAIL DRIVING CONFIGURATIONS

(I/O test circuit of Figures 2 and 3, C_{LOAD} = 15 pF, driver output impedance \leq 50 Ω , R_{LOAD} = 1 M Ω)

			-40°C to +85°C (Notes 3 and 4)			
Symbol	Parameter	Parameter Test Conditions Min Typ		Тур	Max	Unit
V _L = 3.6 V, \	/ _{CC} = 2.5 V	·				
t _{RVCC}	I/O V _{CC} Risetime				15	ns
t _{FVCC}	I/O V _{CC} Falltime				10	ns
t _{RVL}	I/O V _L Risetime				15	ns
t _{FVL}	I/O V _L Falltime				15	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				15	ns
t _{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s
V _L = 5.5 V, \	/ _{CC} = 1.5 V					
t _{RVCC}	I/O V _{CC} Risetime				30	ns
t _{FVCC}	I/O V _{CC} Falltime				10	ns
t _{RVL}	I/O V _L Risetime				15	ns
t _{FVL}	I/O V _L Falltime				20	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V _L)				20	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				20	ns
t _{PPSKEW}	Part-to-Part Skew				5	nS
	Maximum Data Rate		20			Mb/s

3. Typical values are for V_{CC} = +3.3 V, V_L = +1.8 V and T_A = +25°C. 4. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

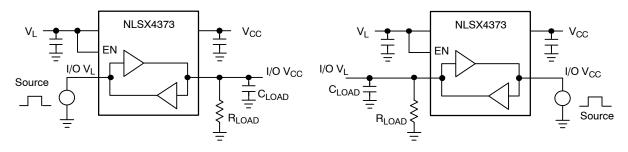
TIMING CHARACTERISTICS - OPEN DRAIN DRIVING CONFIGURATIONS

(I/O test circuit of Figures 4 and 5, C_{LOAD} = 15 pF, driver output impedance \leq 50 Ω , R_{LOAD} = 1 M Ω)

			-40°C to +85°C (Notes 5 and 6)				
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit	
$+1.5 \le V_L \le V_{CC} \le +5.5 V$							
t _{RVCC}	I/O V _{CC} Risetime				400	ns	
t _{FVCC}	I/O V _{CC} Falltime				50	ns	
t _{RVL}	I/O V _L Risetime				400	ns	
t _{FVL}	I/O V _L Falltime				60	ns	
t _{PDVL-VCC}	Propagation Delay (Driving I/O VL)				1000	ns	
t _{PDVCC-VL}	Propagation Delay (Driving I/O V _{CC})				1000	ns	
t PPSKEW	Part-to-Part Skew				50	nS	
MDR	Maximum Data Rate		2			Mb/s	

Typical values are for V_{CC} = +3.3 V, V_L = +1.8 V and T_A = +25°C.
 All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

TEST SETUPS



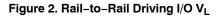


Figure 3. Rail-to-Rail Driving I/O V_{CC}

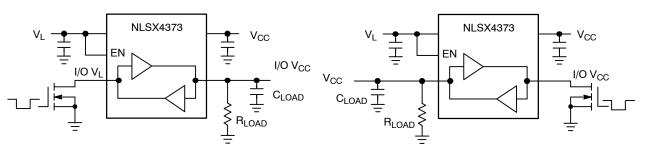


Figure 4. Open–Drain Driving I/O $\rm V_L$

Figure 5. Open–Drain Driving I/O V_{CC}

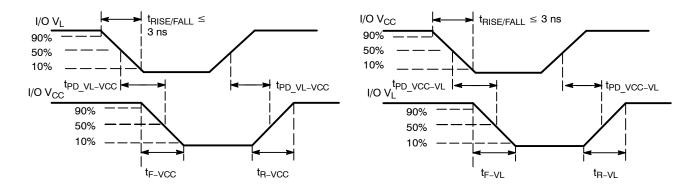
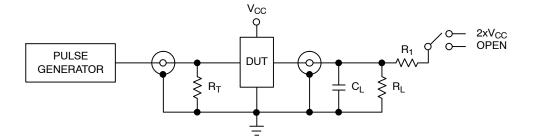


Figure 6. Definition of Timing Specification Parameters



Test	Switch
t _{PZH} , t _{PHZ}	Open
t _{PZL} , t _{PLZ}	$2 \times V_{CC}$

 C_L = 15 pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 50 k Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

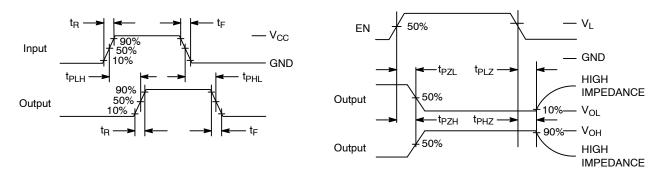


Figure 7. Test Circuit for Enable/Disable Time Measurement

Figure 8. Timing Definitions for Propagation Delays and Enable/Disable Measurement

APPLICATIONS INFORMATION

Level Translator Architecture

The NLSX4373 auto sense translator provides bi-directional voltage level shifting to transfer data in multiple supply voltage systems. This device has two supply voltages, V_L and V_{CC} , which set the logic levels on the input and output sides of the translator. When used to transfer data from the V_L to the V_{CC} ports, input signals referenced to the V_L supply are translated to output signals with a logic level matched to V_{CC} . In a similar manner, the V_{CC} to V_L translation shifts input signals with a logic level compatible to V_{CC} to an output signal matched to V_L .

The NLSX4373 consists of two bi-directional channels that independently determine the direction of the data flow without requiring a directional pin. The one-shot circuits are used to detect the rising or falling input signals. In addition, the one shots decrease the rise and fall time of the output signal for high-to-low and low-to-high transitions.

Each input/output channel has an internal 10 k Ω pull. The magnitude of the pullup resistors can be reduced by connecting external resistors in parallel to the internal 10 k Ω resistors.

Input Driver Requirements

The rise (t_R) and fall (t_F) timing parameters of the open drain outputs depend on the magnitude of the pull-up resistors. In addition, the propagation times (t_{PD}) , skew (t_{PSKEW}) and maximum data rate depend on the impedance of the device that is connected to the translator. The timing parameters listed in the data sheet assume that the output impedance of the drivers connected to the translator is less than 50 k Ω .

Enable Input (EN)

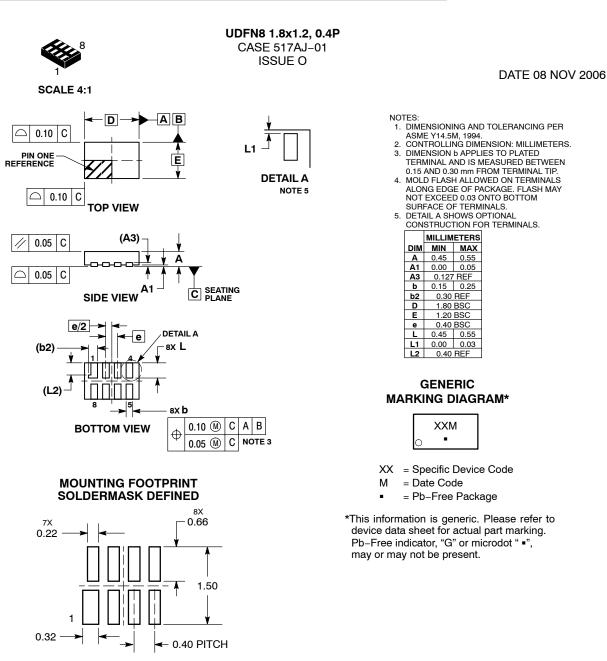
The NLSX4373 has an Enable pin (EN) that provides tri-state operation at the I/O pins. Driving the Enable pin to a low logic level minimizes the power consumption of the device and drives the I/O V_{CC} and I/O V_L pins to a high impedance state. Normal translation operation occurs when the EN pin is equal to a logic high signal. The EN pin is referenced to the V_L supply and has Overvoltage Tolerant (OVT) protection.

Power Supply Guidelines

During normal operation, supply voltage V_L can be greater than, less than or equal to V_{CC} . The sequencing of the power supplies will not damage the device during the power up operation.

For optimal performance, 0.01 μ F to 0.1 μ F decoupling capacitors should be used on the V_L and V_{CC} power supply pins. Ceramic capacitors are a good design choice to filter and bypass any noise signals on the voltage lines to the ground plane of the PCB. The noise immunity will be maximized by placing the capacitors as close as possible to the supply and ground pins, along with minimizing the PCB connection traces.





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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

COLLECTOR, #2

COLLECTOR, #1

COLLECTOR, #1

6.

7.

8

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